/ Revised record

A	2018-12-18				
B	2019-4-20				
C	2019-7-24	1			
D	2021-10-26	4			

/ Descriptions

SOT-363 NPN+PNP

Double silicon NPN and PNP transistor in a SOT-363 Plastic Package.

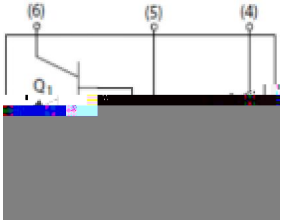
/ Features

Ideal for Low Power Amplification and Switching.HF Product.

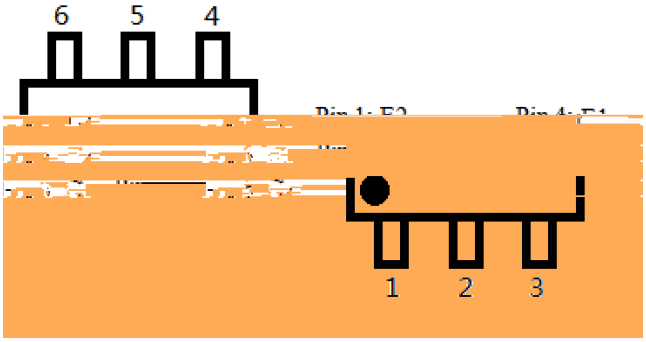
/ Applications

Power amplifier application.

/ Equivalent Circuit



/ Pinning



/ h_{FE} Classifications & Marking

See Marking Instructions.

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Total Power Dissipation	P_d	200	mW
Thermal Resistance, Junction to Ambient	R θ JA	625	/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 150	

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	75	V
Collector to Emitter Voltage	V_{CEO}	40	VE E

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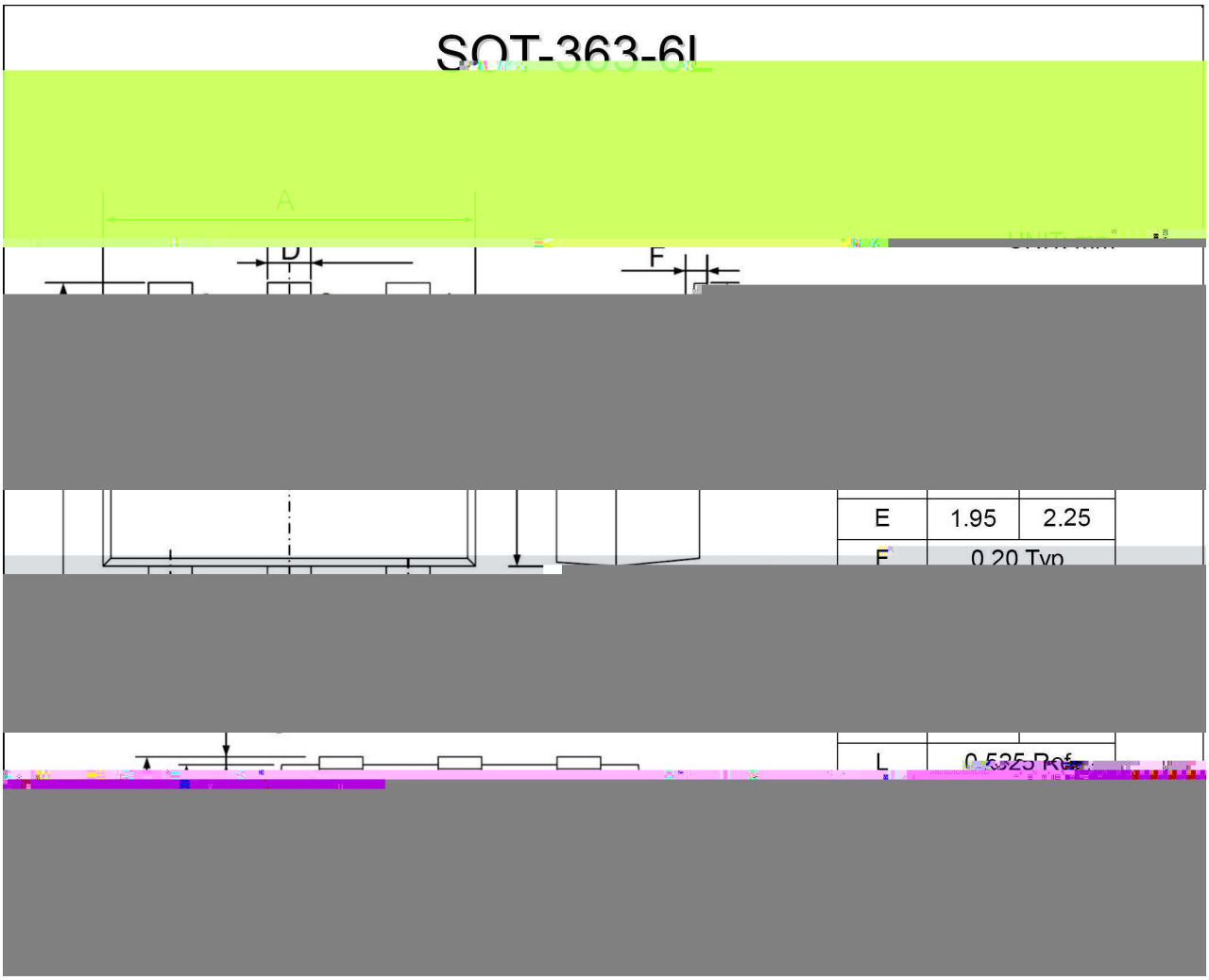
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Rev.D Oct.-2021

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/ Package Dimensions



/ Marking Instructions

●

Note:

● 7

Product Type Code

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Note:

1 150 180 60 90sec;
1.Preheating:150~180℃, Time:60~90sec.

2 245±5 5±0.5sec;
2.Peak Temp.:245±5℃, Duration:5±0.5sec.

3 2 10℃/sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

260±5℃ 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC. · Cn F n

/ REEL

Package Type !	Units " # $					Dimension " % & (unit ' mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box (	Outer Box)
	[illegible]	10	30,000	6	180000			